

NPN Silicon Transistor

Symbol	Parameter	Value	Units
V _{CBO}	Collector -Base Voltage	70	V
V _{CEO}	Collector-Emitter Voltage	60	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current	10	A
IB	Base Current	6	А
P _C	Collector Dissipation (T _C =25°C)	75	W
P _C P _C	Collector Dissipation (T _a =25°C)	0.6	W
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

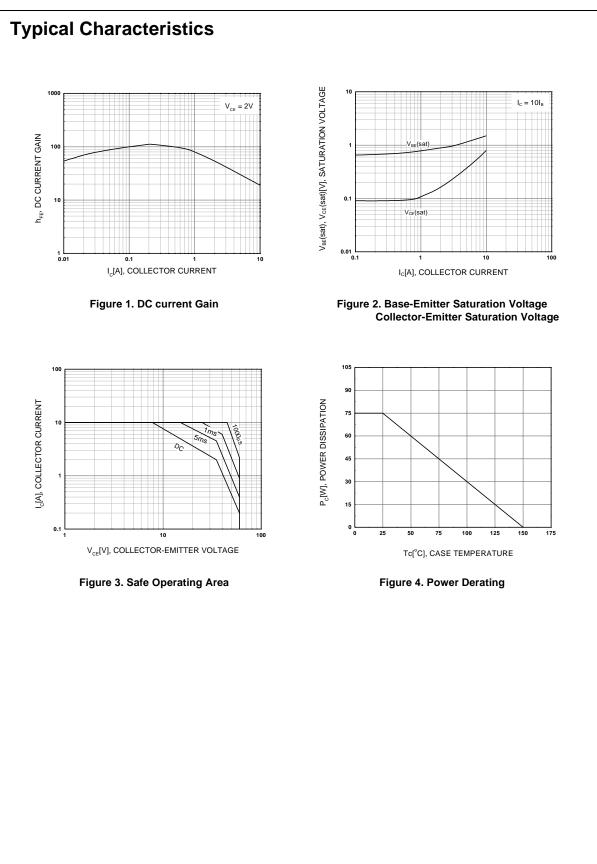
Absolute Maximum Ratings Tc=25°C unless otherwise noted

Electrical Characteristics T_C=25°C unless otherwise noted

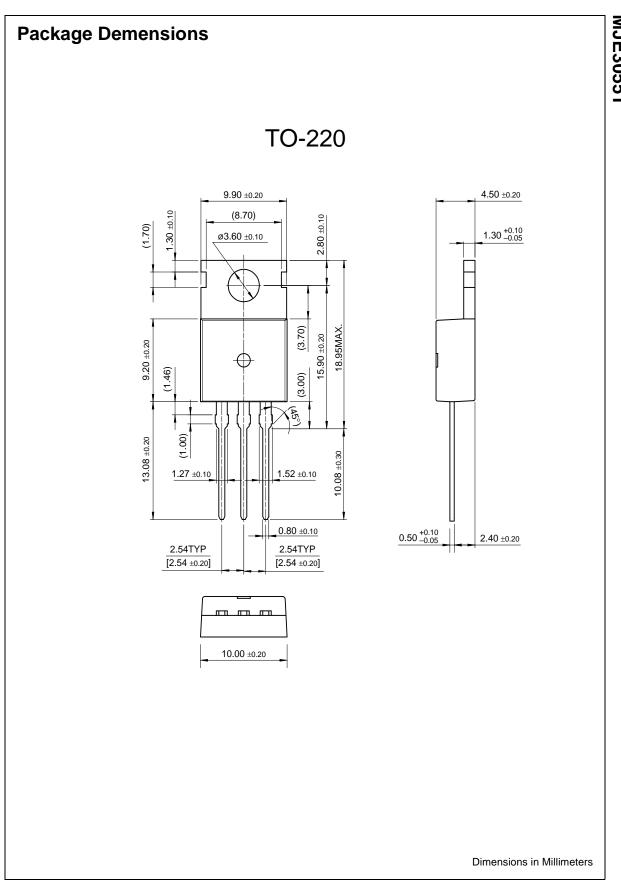
Symbol	Parameter	Test Condition	Min.	Max.	Units
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 200 {\rm mA}, I_{\rm B} = 0$	60		V
I _{CEO}	Collector Cut-off Current	$V_{CE} = 30V, I_B = 0$		700	μΑ
ICEX1 ICEX2	Collector Cut-off Current	$V_{CE} = 70V, V_{BE}(off) = -1.5V$ $V_{CE} = 70V, V_{BE}(off) = -1.5V$ @ T _C = 150°C		1 5	mA mA
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$		5	mA
h _{FE}	*DC Current Gain	$V_{CE} = 4V, I_C = 4A$ $V_{CE} = 4V, I_C = 10A$	20 5	100	C-n.
V _{CE} (sat)	*Collector-Emitter Saturation Voltage	$I_{C} = 4A, I_{B} = 0.4A$ $I_{C} = 10A, I_{B} = 3.3A$		1.1 8	V V
V _{BE} (on)	*Base-Emitter On Voltage	$V_{CE} = 4V$, $I_C = 4A$		1.8	V
f _T	Current Gain Bandwidth Product	$V_{CE} = 10V, I_{C} = 500mA$	2		MHz

WWW.DZSC * Pulse test: PW≤300µs, duty cycle≤2% Pulse





MJE3055T



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